

L Number	Hits	Search Text	DB	Time stamp
1	2690	257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.	USPAT; US-PGPUB	2004/11/05 11:52
2	522	((msq (methyl adj silsesquioxane)) and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 11:56
3	304	((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)") and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:46
4	83	((polymeric adj alkyl adj siloxane) sioch sicoh) and ((polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:04
5	39	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:07
6	323	(257/\$.ccls. 438/\$.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch sich (polymeric adj silicon adj carbide) "sic(h)")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:10
7	47	MIKAGI-K MIKAGI-KAORU	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/05 13:23
8	49	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((silicon wafer semiconductor) and (damascene inlaid "in-laid") and ((copper cu) same seed same (electroplat\$3 plat43) same (cmp planar\$8)))	USPAT; US-PGPUB	2004/11/05 13:24
9	53	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and (((dielectric insulat\$4 oxide dioxide sioch sicoh sich "low-k" "low k") near4 barrier) with (reduc\$5 redox deoxid\$7))	USPAT; US-PGPUB	2004/11/05 13:25
10	22	((copper cu) near2 (plat\$6 electroplat\$6)) with (seed near2 (tan tin ((tantalum titanium) adj nitride)))	USPAT; US-PGPUB	2004/11/05 13:27